

Excellent Integrated System Limited

Stocking Distributor

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Vishay/Siliconix SI6410DQ-T1-E3

For any questions, you can email us directly: <u>sales@integrated-circuit.com</u>



Distributor of Vishay/Siliconix: Excellent Integrated System Limited Datasheet of SI6410DQ-T1-E3 - MOSFET N-CH 30V 7.8A 8-TSSOP Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



Si6410DQ

Vishay Siliconix

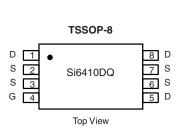
N-Channel 30-V (D-S) MOSFET

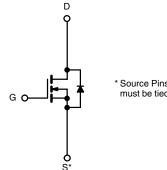
PRODUCT SUMMARY			
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	
30	0.014 at V _{GS} = 10 V	± 7.8	
30	0.021 at V _{GS} = 4.5 V	± 6.3	

FEATURES

- Halogen-free
- TrenchFET[®] Power MOSFETs







Source Pins 2, 3, 6 and 7 must be tied common.

Ordering Information: Si6410DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25 \text{ °C}$, unless otherwise noted					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	30	- v	
Gate-Source Voltage		V _{GS}	± 20		
	T _A = 25 °C	- I _D	± 7.8		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		± 6.2		
Pulsed Drain Current		I _{DM}	± 30	- A -	
Continuous Source Current (Diode Conduction) ^a		۱ _S	1.5		
	T _A = 25 °C	P	1.5	w	
Maximum Power Dissipation ^a	T _A = 70 °C	- P _D -	1.0	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient ^a	R _{thJA}	83	°C/W

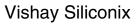
Notes:

a. Surface Mounted on FR4 board, t \leq 10 s.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm.



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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1			V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	20 00		1	μA
		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			25	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	20			Α
Drain-Source On-State Resistance ^a		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 7.8 \text{ A}$		0.011	0.014	Ω
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 5 \text{ A}$		0.015	0.021	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 7.8 A		27		S
Diode Forward Voltage ^a	V _{SD}	I _S = 1.5 A, V _{GS} = 0 V		0.7	1.1	V
Dynamic ^b						
Gate Charge	Qg	$V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 7.8 \text{ A}$		22	33	nC
Total Gate Charge	Q _{gt}			43	60	
Gate-Source Charge	Q _{gs}	V_{DS} = 15 V, V_{GS} = 10 V, I_{D} = 7.8 A		9.0		
Gate-Drain Charge	Q _{gd}			7.0		
Turn-On Delay Time	t _{d(on)}			15	30	ns
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		10	20	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ 1 A, V_{GEN} = 10 V, R_G = 6 Ω		70	120	
Fall Time	t _f			20	50	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.5 A, di/dt = 100 A/μs		50	80	

Notes: a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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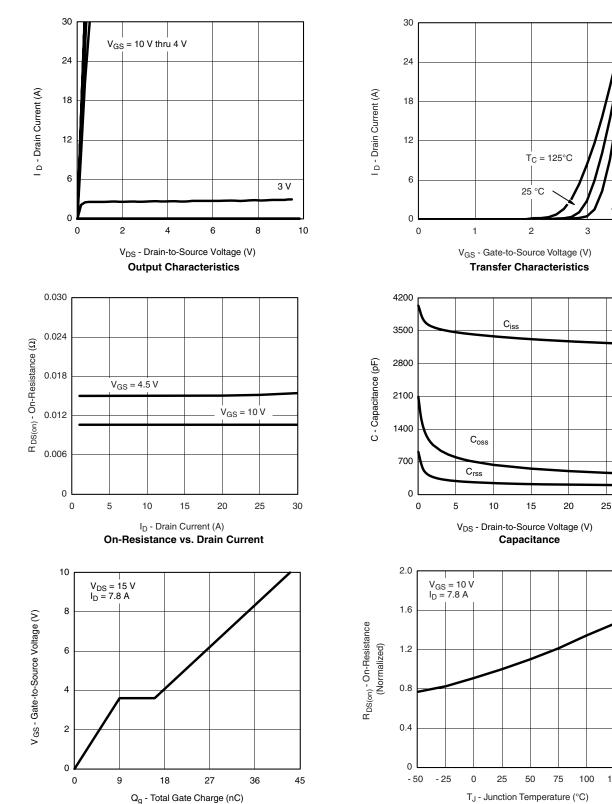


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- 55 °C

4

30



TYPICAL CHARACTERISTICS 25 °C unless noted

Document Number: 70661 S-80682-Rev. D, 31-Mar-08 Gate Charge

125

On-Resistance vs. Junction Temperature

150

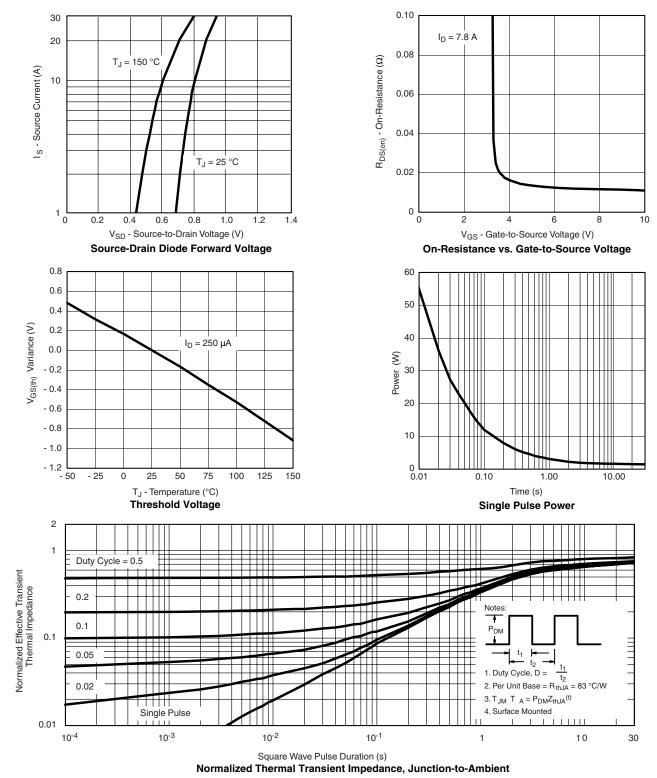


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